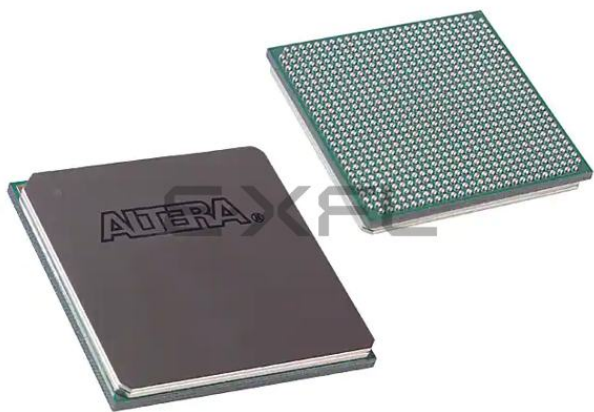




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	1846
Number of Logic Elements/Cells	18460
Total RAM Bits	1669248
Number of I/O	586
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	780-BBGA, FCBGA
Supplier Device Package	780-FBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1s20f780i6

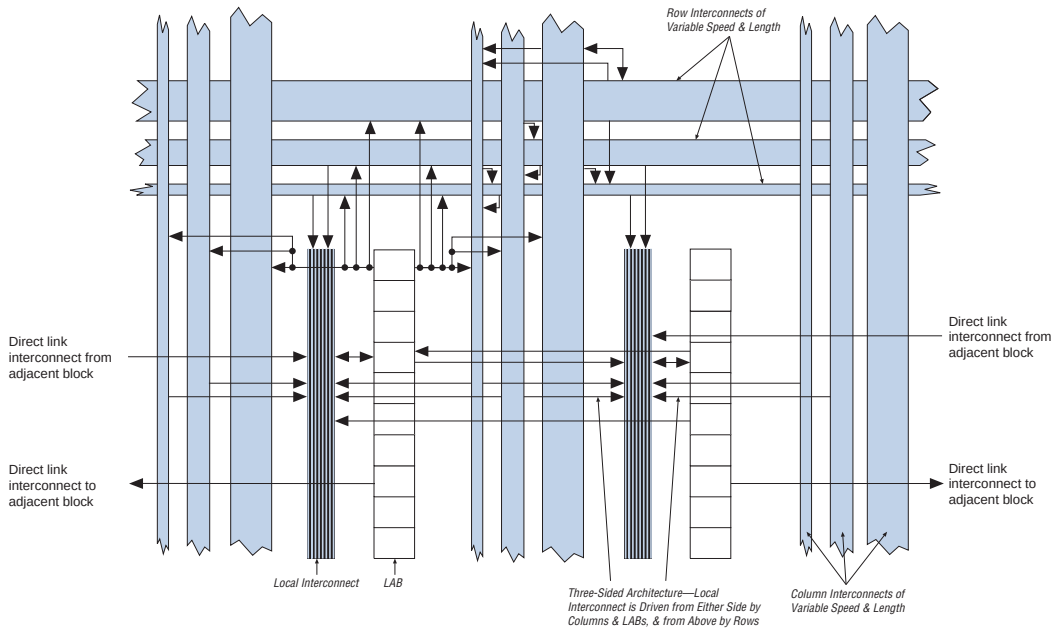
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Figure 2–2. Stratix LAB Structure

LAB Interconnects

The LAB local interconnect can drive LEs within the same LAB. The LAB local interconnect is driven by column and row interconnects and LE outputs within the same LAB. Neighboring LABs, M512 RAM blocks, M4K RAM blocks, or DSP blocks from the left and right can also drive an LAB's local interconnect through the direct link connection. The direct link connection feature minimizes the use of row and column interconnects, providing higher performance and flexibility. Each LE can drive 30 other LEs through fast local and direct link interconnects.

Figure 2–3 shows the direct link connection.

asynchronous load, and clear signals. An asynchronous clear signal takes precedence if both signals are asserted simultaneously. Each LAB supports up to two clears and one preset signal.

In addition to the clear and preset ports, Stratix devices provide a chip-wide reset pin (DEV_CLRn) that resets all registers in the device. An option set before compilation in the Quartus II software controls this pin. This chip-wide reset overrides all other control signals.

MultiTrack Interconnect

In the Stratix architecture, connections between LEs, TriMatrix memory, DSP blocks, and device I/O pins are provided by the MultiTrack interconnect structure with DirectDrive™ technology. The MultiTrack interconnect consists of continuous, performance-optimized routing lines of different lengths and speeds used for inter- and intra-design block connectivity. The Quartus II Compiler automatically places critical design paths on faster interconnects to improve design performance.

DirectDrive technology is a deterministic routing technology that ensures identical routing resource usage for any function regardless of placement within the device. The MultiTrack interconnect and DirectDrive technology simplify the integration stage of block-based designing by eliminating the re-optimization cycles that typically follow design changes and additions.

The MultiTrack interconnect consists of row and column interconnects that span fixed distances. A routing structure with fixed length resources for all devices allows predictable and repeatable performance when migrating through different device densities. Dedicated row interconnects route signals to and from LABs, DSP blocks, and TriMatrix memory within the same row. These row resources include:

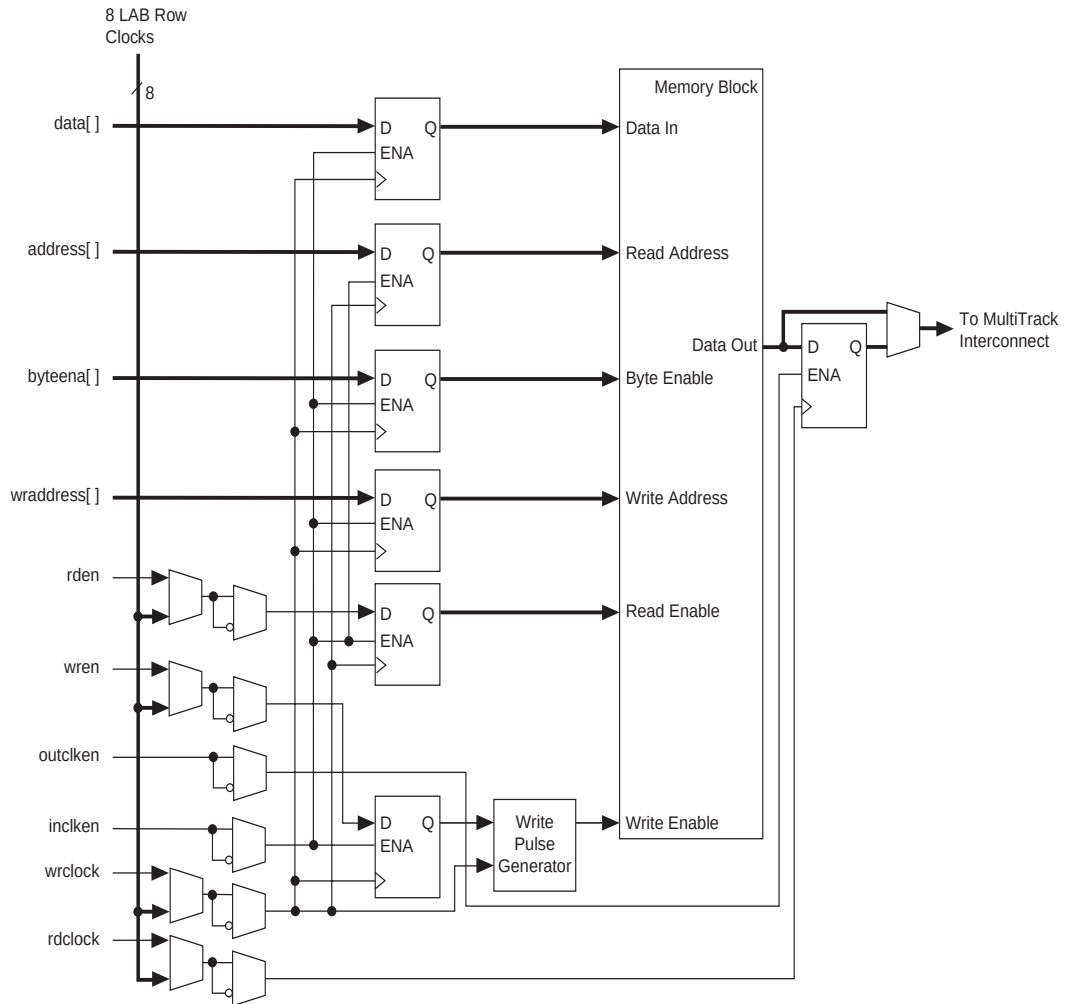
- Direct link interconnects between LABs and adjacent blocks.
- R4 interconnects traversing four blocks to the right or left.
- R8 interconnects traversing eight blocks to the right or left.
- R24 row interconnects for high-speed access across the length of the device.

The direct link interconnect allows an LAB, DSP block, or TriMatrix memory block to drive into the local interconnect of its left and right neighbors and then back into itself. Only one side of a M-RAM block interfaces with direct link and row interconnects. This provides fast communication between adjacent LABs and/or blocks without using row interconnect resources.

The R4 interconnects span four LABs, three LABs and one M512 RAM block, two LABs and one M4K RAM block, or two LABs and one DSP block to the right or left of a source LAB. These resources are used for fast

Table 2–2 shows the Stratix device’s routing scheme.

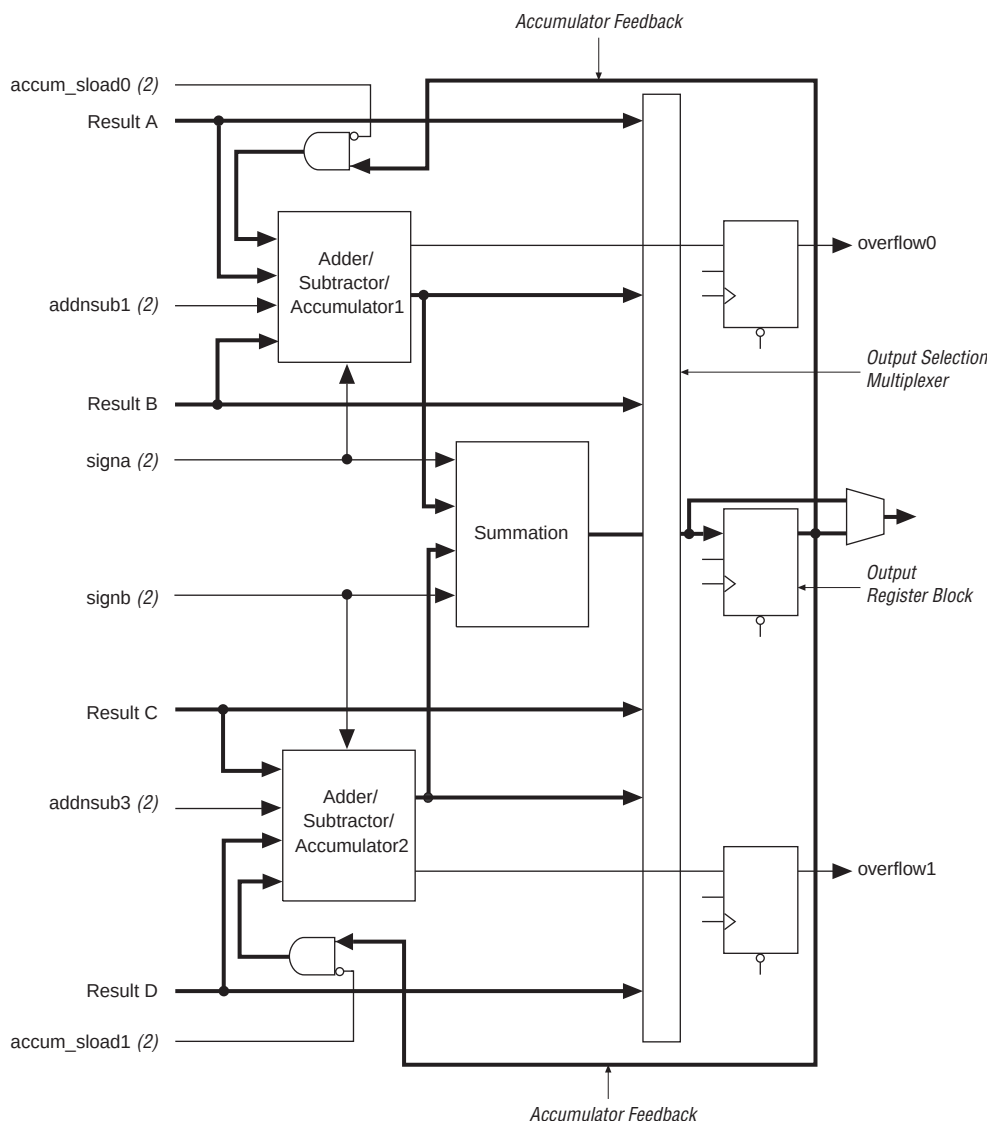
Table 2–2. Stratix Device Routing Scheme																	
Source	Destination																
	LUT Chain	Register Chain	Local Interconnect	Direct Link Interconnect	R4 Interconnect	R8 Interconnect	R24 Interconnect	C4 Interconnect	C8 Interconnect	C16 Interconnect	LE	M512 RAM Block	M4K RAM Block	M-RAM Block	DSP Blocks	Column IOE	Row IOE
LUT Chain											✓						
Register Chain											✓						
Local Interconnect											✓	✓	✓	✓	✓	✓	✓
Direct Link Interconnect			✓														
R4 Interconnect			✓		✓		✓	✓		✓							
R8 Interconnect			✓			✓			✓								
R24 Interconnect					✓		✓	✓		✓							
C4 Interconnect			✓		✓			✓									
C8 Interconnect			✓			✓			✓								
C16 Interconnect					✓		✓	✓		✓							
LE	✓	✓	✓	✓	✓	✓		✓	✓								
M512 RAM Block			✓	✓	✓	✓		✓	✓								
M4K RAM Block			✓	✓	✓	✓		✓	✓								
M-RAM Block								✓	✓								
DSP Blocks			✓	✓	✓	✓		✓	✓								
Column IOE				✓				✓	✓	✓							
Row IOE				✓		✓	✓	✓	✓	✓							

Figure 2–26. Input/Output Clock Mode in Simple Dual-Port Mode *Notes (1), (2)***Notes to Figure 2–26:**

- (1) All registers shown except the rden register have asynchronous clear ports.
- (2) Violating the setup or hold time on the address registers could corrupt the memory contents. This applies to both read and write operations.

Read/Write Clock Mode

The memory blocks implement read/write clock mode for simple dual-port memory. You can use up to two clocks in this mode. The write clock controls the block's data inputs, *wraddress*, and *wren*. The read clock controls the data output, *rdaddress*, and *rden*. The memory blocks support independent clock enables for each clock and asynchronous clear signals for the read- and write-side registers. [Figure 2–27](#) shows a memory block in read/write clock mode.

Figure 2–34. Adder/Output Blocks *Note (1)***Notes to Figure 2–34:**

- (1) Adder/output block shown in Figure 2–34 is in 18×18 -bit mode. In 9×9 -bit mode, there are four adder/subtractor blocks and two summation blocks.
- (2) These signals are either not registered, registered once, or registered twice to match the data path pipeline.

provide general purpose clocking with multiplication and phase shifting as well as high-speed outputs for high-speed differential I/O support. Enhanced and fast PLLs work together with the Stratix high-speed I/O and advanced clock architecture to provide significant improvements in system performance and bandwidth.

The Quartus II software enables the PLLs and their features without requiring any external devices. Table 2–18 shows the PLLs available for each Stratix device.

Table 2–18. Stratix Device PLL Availability

Device	Fast PLLs								Enhanced PLLs			
	1	2	3	4	7	8	9	10	5(1)	6(1)	11(2)	12(2)
EP1S10	✓	✓	✓	✓					✓	✓		
EP1S20	✓	✓	✓	✓					✓	✓		
EP1S25	✓	✓	✓	✓					✓	✓		
EP1S30	✓	✓	✓	✓	✓ (3)	✓ (3)	✓ (3)	✓ (3)	✓	✓		
EP1S40	✓	✓	✓	✓	✓ (3)	✓ (3)	✓ (3)	✓ (3)	✓	✓	✓ (3)	✓ (3)
EP1S60	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
EP1S80	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓

Notes to Table 2–18:

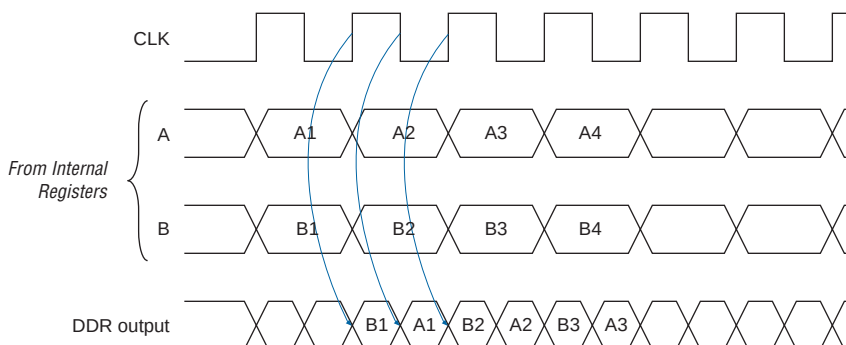
- (1) PLLs 5 and 6 each have eight single-ended outputs or four differential outputs.
- (2) PLLs 11 and 12 each have one single-ended output.
- (3) EP1S30 and EP1S40 devices do not support these PLLs in the 780-pin FineLine BGA® package.

Clock Multiplication & Division

Each Stratix device enhanced PLL provides clock synthesis for PLL output ports using $m/(n \times \text{post-scale counter})$ scaling factors. The input clock is divided by a pre-scale divider, n , and is then multiplied by the m feedback factor. The control loop drives the VCO to match $f_{\text{IN}} \times (m/n)$. Each output port has a unique post-scale counter that divides down the high-frequency VCO. For multiple PLL outputs with different frequencies, the VCO is set to the least common multiple of the output frequencies that meets its frequency specifications. Then, the post-scale dividers scale down the output frequency for each output port. For example, if output frequencies required from one PLL are 33 and 66 MHz, set the VCO to 330 MHz (the least common multiple in the VCO's range). There is one pre-scale counter, n , and one multiply counter, m , per PLL, with a range of 1 to 512 on each. There are two post-scale counters (l) for regional clock output ports, four counters (g) for global clock output ports, and up to four counters (e) for external clock outputs, all ranging from 1 to 1024 with a 50% duty cycle setting. The post-scale counters range from 1 to 512 with any non-50% duty cycle setting. The Quartus II software automatically chooses the appropriate scaling factors according to the input frequency, multiplication, and division values entered.

Clock Switchover

To effectively develop high-reliability network systems, clocking schemes must support multiple clocks to provide redundancy. For this reason, Stratix device enhanced PLLs support a flexible clock switchover capability. [Figure 2–53](#) shows a block diagram of the switchover circuit. The switchover circuit is configurable, so you can define how to implement it. Clock-sense circuitry automatically switches from the primary to secondary clock for PLL reference when the primary clock signal is not present.

Figure 2–68. Output Timing Diagram in DDR Mode

The Stratix IOE operates in bidirectional DDR mode by combining the DDR input and DDR output configurations. Stratix device I/O pins transfer data on a DDR bidirectional bus to support DDR SDRAM. The negative-edge-clocked OE register holds the OE signal inactive until the falling edge of the clock. This is done to meet DDR SDRAM timing requirements.

External RAM Interfacing

Stratix devices support DDR SDRAM at up to 200 MHz (400-Mbps data rate) through dedicated phase-shift circuitry, QDR and QDRII SRAM interfaces up to 167 MHz, and ZBT SRAM interfaces up to 200 MHz. Stratix devices also provide preliminary support for reduced latency DRAM II (RLDRAM II) at rates up to 200 MHz through the dedicated phase-shift circuitry.



In addition to the required signals for external memory interfacing, Stratix devices offer the optional clock enable signal. By default the Quartus II software sets the clock enable signal high, which tells the output register to update with new values. The output registers hold their own values if the design sets the clock enable signal low. See [Figure 2–64](#).



To find out more about the DDR SDRAM specification, see the JEDEC web site (www.jedec.org). For information on memory controller megafunctions for Stratix devices, see the Altera web site (www.altera.com). See *AN 342: Interfacing DDR SDRAM with Stratix & Stratix GX Devices* for more information on DDR SDRAM interface in Stratix. Also see *AN 349: QDR SRAM Controller Reference Design for Stratix & Stratix GX Devices* and *AN 329: ZBT SRAM Controller Reference Design for Stratix & Stratix GX Devices*.

The only way you can use the `rx_data_align` is if one of the following is true:

- The receiver PLL is only clocking receive channels (no resources for the transmitter)
- If all channels can fit in one I/O bank

Table 2–38. EP1S30 Differential Channels *Note (1)*

Package	Transmitter/Receiver	Total Channels	Maximum Speed (Mbps)	Center Fast PLLs				Corner Fast PLLs (2), (3)			
				PLL1	PLL2	PLL3	PLL4	PLL7	PLL8	PLL9	PLL10
780-pin FineLine BGA	Transmitter (4)	70	840	18	17	17	18	(6)	(6)	(6)	(6)
			840 (5)	35	35	35	35	(6)	(6)	(6)	(6)
	Receiver	66	840	17	16	16	17	(6)	(6)	(6)	(6)
			840 (5)	33	33	33	33	(6)	(6)	(6)	(6)
956-pin BGA	Transmitter (4)	80	840	19	20	20	19	20	20	20	20
			840 (5)	39	39	39	39	20	20	20	20
	Receiver	80	840	20	20	20	20	19	20	20	19
			840 (5)	40	40	40	40	19	20	20	19
1,020-pin FineLine BGA	Transmitter (4)	80 (2) (7)	840	19 (1)	20	20	19 (1)	20	20	20	20
			840 (5),(8)	39 (1)	39 (1)	39 (1)	39 (1)	20	20	20	20
	Receiver	80 (2) (7)	840	20	20	20	20	19 (1)	20	20	19 (1)
			840 (5),(8)	40	40	40	40	19 (1)	20	20	19 (1)

Table 2–39. EP1S40 Differential Channels (Part 1 of 2) *Note (1)*

Package	Transmitter/Receiver	Total Channels	Maximum Speed (Mbps)	Center Fast PLLs				Corner Fast PLLs (2), (3)			
				PLL1	PLL2	PLL3	PLL4	PLL7	PLL8	PLL9	PLL10
780-pin FineLine BGA	Transmitter (4)	68	840	18	16	16	18	(6)	(6)	(6)	(6)
			840 (5)	34	34	34	34	(6)	(6)	(6)	(6)
	Receiver	66	840	17	16	16	17	(6)	(6)	(6)	(6)
			840 (5)	33	33	33	33	(6)	(6)	(6)	(6)

Table 4–2. Stratix Device Recommended Operating Conditions (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	(4), (5)	3.00 (3.135)	3.60 (3.465)	V
	Supply voltage for output buffers, 2.5-V operation	(4)	2.375	2.625	V
	Supply voltage for output buffers, 1.8-V operation	(4)	1.71	1.89	V
	Supply voltage for output buffers, 1.5-V operation	(4)	1.4	1.6	V
V_I	Input voltage	(3), (6)	–0.5	4.0	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Operating junction temperature	For commercial use	0	85	°C
		For industrial use	–40	100	°C

Table 4–3. Stratix Device DC Operating Conditions Note (7) (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
I_I	Input pin leakage current	$V_I = V_{CCIOmax}$ to 0 V (8)	–10		10	μA
I_{OZ}	Tri-stated I/O pin leakage current	$V_O = V_{CCIOmax}$ to 0 V (8)	–10		10	μA
I_{CC0}	V_{CC} supply current (standby) (All memory blocks in power-down mode)	V_I = ground, no load, no toggling inputs				mA
		EP1S10. V_I = ground, no load, no toggling inputs		37		mA
		EP1S20. V_I = ground, no load, no toggling inputs		65		mA
		EP1S25. V_I = ground, no load, no toggling inputs		90		mA
		EP1S30. V_I = ground, no load, no toggling inputs		114		mA
		EP1S40. V_I = ground, no load, no toggling inputs		145		mA
		EP1S60. V_I = ground, no load, no toggling inputs		200		mA
		EP1S80. V_I = ground, no load, no toggling inputs		277		mA

Table 4–25. 3.3-V AGP 1× Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V _{OH}	High-level output voltage	I _{OUT} = –0.5 mA	0.9 × V _{CCIO}		3.6	V
V _{OL}	Low-level output voltage	I _{OUT} = 1.5 mA			0.1 × V _{CCIO}	V

Table 4–26. 1.5-V HSTL Class I Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V _{CCIO}	Output supply voltage		1.4	1.5	1.6	V
V _{REF}	Input reference voltage		0.68	0.75	0.9	V
V _{TT}	Termination voltage		0.7	0.75	0.8	V
V _{IH} (DC)	DC high-level input voltage		V _{REF} + 0.1			V
V _{IL} (DC)	DC low-level input voltage		–0.3		V _{REF} – 0.1	V
V _{IH} (AC)	AC high-level input voltage		V _{REF} + 0.2			V
V _{IL} (AC)	AC low-level input voltage				V _{REF} – 0.2	V
V _{OH}	High-level output voltage	I _{OH} = –8 mA (3)	V _{CCIO} – 0.4			V
V _{OL}	Low-level output voltage	I _{OL} = 8 mA (3)			0.4	V

Table 4–27. 1.5-V HSTL Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V _{CCIO}	Output supply voltage		1.4	1.5	1.6	V
V _{REF}	Input reference voltage		0.68	0.75	0.9	V
V _{TT}	Termination voltage		0.7	0.75	0.8	V
V _{IH} (DC)	DC high-level input voltage		V _{REF} + 0.1			V
V _{IL} (DC)	DC low-level input voltage		–0.3		V _{REF} – 0.1	V
V _{IH} (AC)	AC high-level input voltage		V _{REF} + 0.2			V
V _{IL} (AC)	AC low-level input voltage				V _{REF} – 0.2	V
V _{OH}	High-level output voltage	I _{OH} = –16 mA (3)	V _{CCIO} – 0.4			V
V _{OL}	Low-level output voltage	I _{OL} = 16 mA (3)			0.4	V

device. Decoupling capacitors were not used in this measurement. To factor in the current for decoupling capacitors, sum up the current for each capacitor using the following equation:

$$I = C (dV/dt)$$

If the regulator or power supply minimum output current is more than the Stratix device requires, then the device may consume more current than the maximum current listed in Table 4–34. However, the device does not require any more current to successfully power up than what is listed in Table 4–34.

Table 4–34. Stratix Power-Up Current (I_{CCINT}) Requirements *Note (1)*

Device	Power-Up Current Requirement		Unit
	Typical	Maximum	
EP1S10	250	700	mA
EP1S20	400	1,200	mA
EP1S25	500	1,500	mA
EP1S30	550	1,900	mA
EP1S40	650	2,300	mA
EP1S60	800	2,600	mA
EP1S80	1,000	3,000	mA

Note to Table 4–34:

- (1) The maximum test conditions are for 0° C and typical test conditions are for 40° C.

The exact amount of current consumed varies according to the process, temperature, and power ramp rate. Stratix devices typically require less current during power up than shown in Table 4–34. The user-mode current during device operation is generally higher than the power-up current.

The duration of the I_{CCINT} power-up requirement depends on the V_{CCINT} voltage supply rise time. The power-up current consumption drops when the V_{CCINT} supply reaches approximately 0.75 V.

Table 4–81. EP1S40 External I/O Timing on Column Pins Using Global Clock Networks

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.126		2.268		2.558		2.930		ns
t_{INH}	0.000		0.000		0.000		0.000		ns
t_{OUTCO}	2.856	5.585	2.856	5.987	2.856	6.541	2.847	7.253	ns
t_{XZ}	2.796	5.459	2.796	5.855	2.796	6.417	2.787	7.138	ns
t_{ZX}	2.796	5.459	2.796	5.855	2.796	6.417	2.787	7.138	ns
t_{INSUPLL}	1.466		1.455		1.711		1.906		ns
t_{INHPLL}	0.000		0.000		0.000		0.000		ns
t_{OUTCOPLL}	1.092	2.345	1.092	2.510	1.092	2.455	1.089	2.473	ns
t_{XZPLL}	1.032	2.219	1.032	2.378	1.032	2.331	1.029	2.358	ns
t_{ZXPLL}	1.032	2.219	1.032	2.378	1.032	2.331	1.029	2.358	ns

Table 4–82. EP1S40 External I/O Timing on Row Pins Using Fast Regional Clock Networks

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.472		2.685		3.083		3.056		ns
t_{INH}	0.000		0.000		0.000		0.000		ns
t_{OUTCO}	2.631	5.258	2.631	5.625	2.631	6.105	2.745	7.324	ns
t_{XZ}	2.658	5.312	2.658	5.681	2.658	6.173	2.772	7.406	ns
t_{ZX}	2.658	5.312	2.658	5.681	2.658	6.173	2.772	7.406	ns

Table 4–89. EP1S60 External I/O Timing on Row Pins Using Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.775		2.990		3.407		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.867	5.644	2.867	6.057	2.867	6.600	NA	NA	ns
t_{XZ}	2.894	5.698	2.894	6.113	2.894	6.668	NA	NA	ns
t_{ZX}	2.894	5.698	2.894	6.113	2.894	6.668	NA	NA	ns
t_{INSUPLL}	1.523		1.577		1.791		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
t_{OUTCOPLL}	1.174	2.507	1.174	2.643	1.174	2.664	NA	NA	ns
t_{XZPLL}	1.201	2.561	1.201	2.699	1.201	2.732	NA	NA	ns
t_{ZXPLL}	1.201	2.561	1.201	2.699	1.201	2.732	NA	NA	ns

Table 4–90. EP1S60 External I/O Timing on Row Pins Using Global Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.232		2.393		2.721		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	3.182	6.187	3.182	6.654	3.182	7.286	NA	NA	ns
t_{XZ}	3.209	6.241	3.209	6.710	3.209	7.354	NA	NA	ns
t_{ZX}	3.209	6.241	3.209	6.710	3.209	7.354	NA	NA	ns
t_{INSUPLL}	1.651		1.612		1.833		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
t_{OUTCOPLL}	1.154	2.469	1.154	2.608	1.154	2.622	NA	NA	ns
t_{XZPLL}	1.181	2.523	1.181	2.664	1.181	2.690	NA	NA	ns
t_{ZXPLL}	1.181	2.523	1.181	2.664	1.181	2.690	NA	NA	ns

Note to Tables 4–85 to 4–90:

(1) Only EP1S25, EP1S30, and EP1S40 devices have the -8 speed grade.

Table 4–95. EP1S80 External I/O Timing on Row Pins Using Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.295		2.454		2.767		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.917	5.732	2.917	6.148	2.917	6.705	NA	NA	ns
t_{XZ}	2.944	5.786	2.944	6.204	2.944	6.773	NA	NA	ns
t_{ZX}	2.944	5.786	2.944	6.204	2.944	6.773	NA	NA	ns
t_{INSUPLL}	1.011		1.161		1.372		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
t_{OUTCOPLL}	1.808	3.169	1.808	3.209	1.808	3.233	NA	NA	ns
t_{XZPLL}	1.835	3.223	1.835	3.265	1.835	3.301	NA	NA	ns
t_{ZXPLL}	1.835	3.223	1.835	3.265	1.835	3.301	NA	NA	ns

Table 4–96. EP1S80 External I/O Timing on Rows Using Pin Global Clock Networks *Note (1)*

Symbol	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	1.362		1.451		1.613		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	3.457	6.665	3.457	7.151	3.457	7.859	NA	NA	ns
t_{XZ}	3.484	6.719	3.484	7.207	3.484	7.927	NA	NA	ns
t_{ZX}	3.484	6.719	3.484	7.207	3.484	7.927	NA	NA	ns
t_{INSUPLL}	0.994		1.143		1.351		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA		ns
t_{OUTCOPLL}	1.821	3.186	1.821	3.227	1.821	3.254	NA	NA	ns
t_{XZPLL}	1.848	3.240	1.848	3.283	1.848	3.322	NA	NA	ns
t_{ZXPLL}	1.848	3.240	1.848	3.283	1.848	3.322	NA	NA	ns

Note to Tables 4–91 to 4–96:

(1) Only EP1S25, EP1S30, and EP1S40 devices have the -8 speed grade.

Table 4–122. Stratix Maximum Output Clock Rate for PLL[5, 6, 11, 12] Pins in Wire-Bond Packages (Part 2 of 2)

I/O Standard	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Unit
LVDS (2)	311	275	275	MHz
HyperTransport technology (2)	311	275	275	MHz

Table 4–123. Stratix Maximum Output Clock Rate (Using I/O Pins) for PLL[1, 2, 3, 4] Pins in Wire-Bond Packages (Part 1 of 2)

I/O Standard	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Unit
LVTTTL	200	175	175	MHz
2.5 V	200	175	175	MHz
1.8 V	200	175	175	MHz
1.5 V	200	175	175	MHz
LVC MOS	200	175	175	MHz
GTL	125	100	100	MHz
GTL+	125	100	100	MHz
SSTL-3 Class I	110	90	90	MHz
SSTL-3 Class II	150	133	133	MHz
SSTL-2 Class I	90	80	80	MHz
SSTL-2 Class II	110	100	100	MHz
SSTL-18 Class I	110	100	100	MHz
SSTL-18 Class II	110	100	100	MHz
1.5-V HSTL Class I	225	200	200	MHz
1.5-V HSTL Class II	200	167	167	MHz
1.8-V HSTL Class I	225	200	200	MHz
1.8-V HSTL Class II	200	167	167	MHz
3.3-V PCI	200	175	175	MHz
3.3-V PCI-X 1.0	200	175	175	MHz
Compact PCI	200	175	175	MHz
AGP 1×	200	175	175	MHz
AGP 2×	200	175	175	MHz
CTT	125	100	100	MHz
LVPECL (2)	311	270	270	MHz
PCML (2)	400	311	311	MHz

Tables 4-125 and 4-126 show the high-speed I/O timing for Stratix devices.

Table 4-125. High-Speed I/O Specifications for Flip-Chip Packages (Part 1 of 4) Notes (1), (2)														
Symbol	Conditions	-5 Speed Grade			-6 Speed Grade			-7 Speed Grade			-8 Speed Grade			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
f _{HSCLK} (Clock frequency) (LVDS, LVPECL, HyperTransport technology) f _{HSCLK} = f _{HSDR} / W	W = 4 to 30 (Serdes used)	10		210	10		210	10		156	10		115.5	MHz
	W = 2 (Serdes bypass)	50		231	50		231	50		231	50		231	MHz
	W = 2 (Serdes used)	150		420	150		420	150		312	150		231	MHz
	W = 1 (Serdes bypass)	100		462	100		462	100		462	100		462	MHz
	W = 1 (Serdes used)	300		717	300		717	300		624	300		462	MHz
f _{HSDR} Device operation (LVDS, LVPECL, HyperTransport technology)	J = 10	300		840	300		840	300		640	300		462	Mbps
	J = 8	300		840	300		840	300		640	300		462	Mbps
	J = 7	300		840	300		840	300		640	300		462	Mbps
	J = 4	300		840	300		840	300		640	300		462	Mbps
	J = 2	100		462	100		462	100		640	100		462	Mbps
	J = 1 (LVDS and LVPECL only)	100		462	100		462	100		640	100		462	Mbps

Table 4–125. High-Speed I/O Specifications for Flip-Chip Packages (Part 4 of 4) Notes (1), (2)														
Symbol	Conditions	-5 Speed Grade			-6 Speed Grade			-7 Speed Grade			-8 Speed Grade			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
t_{DUTY}	LVDS ($J = 2$ through 10)	47.5	50	52.5	47.5	50	52.5	47.5	50	52.5	47.5	50	52.5	%
	LVDS ($J = 1$) and LVPECL, PCML, HyperTransport technology	45	50	55	45	50	55	45	50	55	45	50	55	%
t_{LOCK}	All			100			100			100			100	μs

Notes to Table 4–125:

- (1) When $J = 4, 7, 8$, and 10, the SERDES block is used.
 (2) When $J = 2$ or $J = 1$, the SERDES is bypassed.